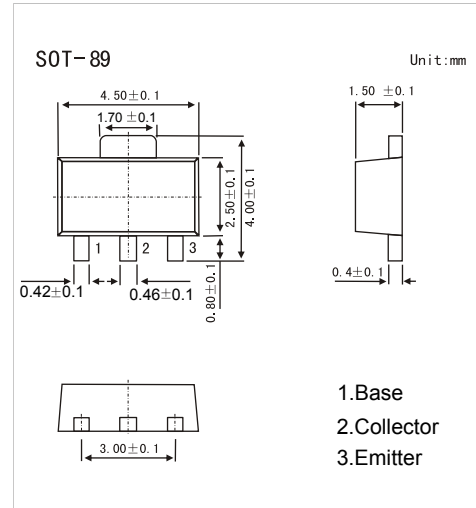


**PNP Transistors**
**2SA1201**
**■ Features**

- High voltage
- High transition frequency
- Complementary to 2SC2881


**■ Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	-120	V
Collector - Emitter Voltage	V <sub>CEO</sub>	-120	
Emitter - Base Voltage	V <sub>EB0</sub>	-5	
Collector Current - Continuous	I <sub>C</sub>	-0.8	A
Collector Power Dissipation	P <sub>C</sub>	0.5	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature range	T <sub>stg</sub>	-55 to 150	

**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>C</sub> = -1mA, I <sub>E</sub> =0	-120			V
Collector- emitter breakdown voltage	V <sub>CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> =0	-120			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -1mA, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -120 V, I <sub>E</sub> =0			-100	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-100	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-1	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-500 mA, I <sub>B</sub> =-50mA			-1.2	
Base - emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =- 5V, I <sub>C</sub> = -500 mA			-1	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA	80		240	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f=1MHz			30	pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA		120		MHz

**■ Classification of h<sub>FE</sub>**

Marking	DO	DY
Rank	O	Y
Range	80-160	120-240

**PNP Transistors**
**2SA1201**
**Typical Characteristics**
